

Silicon NPN Power Transistors

2SC2815

**DESCRIPTION**

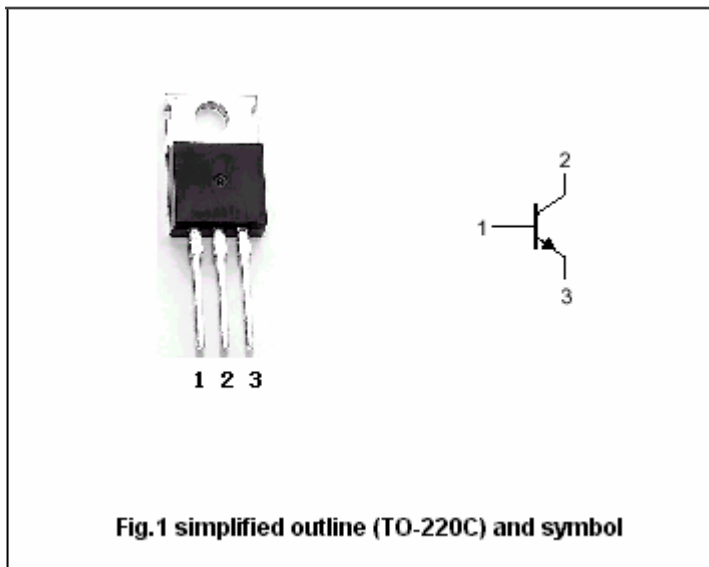
- With TO-220C package
- High voltage;high speed
- Low collector saturation voltage

**APPLICATIONS**

- For use in horizontal deflection output stages of TV's and CTV's circuits

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**Absolut maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	250	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		5	A
$P_{tot}$	Total power dissipation	$T_C=25^\circ C$	40	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-65~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =0	250			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.4A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.4A			1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =300V ; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6.0V ; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2.5A ; V <sub>CE</sub> =5V	40			

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PACKAGE OUTLINE

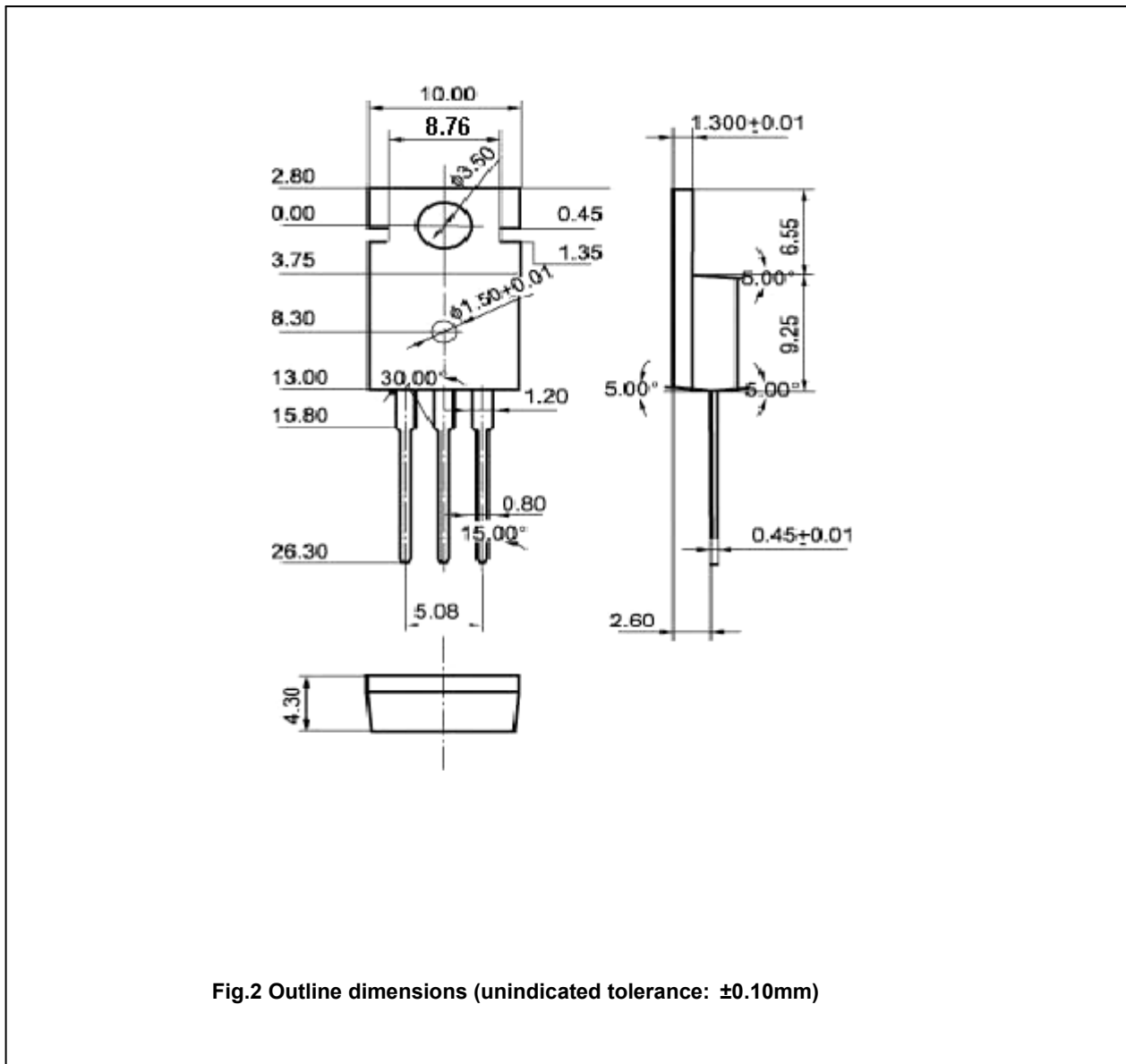


Fig.2 Outline dimensions (unindicated tolerance: ±0.10mm)